ABSTRACT

"Gate electrodes and the formation thereof"

A method of fabricating a gate electrode for a semiconductor comprising the steps of: providing a substrate; providing on the substrate a layer of a first material of thickness t_p, the first material being selected from the group consisting of Si, Si_{1-x}-Ge_x alloy, Ge and mixtures thereof and a layer of metal of thickness t_m; and annealing the layers, such that substantially all of the first material and the metal are consumed during reaction with one another.

[Figure 1]